

Amendments to the Abstract

A chemical vapor deposition (CVD) apparatus for depositing a silicide is disclosed. After a substrate is loaded in a load-lock chamber, the substrate is transferred into a processing chamber. A silicide is deposited on the substrate. After the substrate is transferred into the load-lock chamber, residual gases remaining on the substrate are purged out by flowing air including H₂O (g) from an air purge line connected to the load-lock chamber. The purged residual gases are exhausted by a vacuum pump connected to the air purge line.